

FORM PTO-1449

ATTY. DOCKET NO.

SERIAL NO.

10991002-4

LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

APPLICANT

Tetsuya Takeuchi et al.

FILING DATE

GROUP

Herewith

(Use several sheets if necessary)



REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
DW	AA	5,798,537	08/25/98	Koichi Nitta	257	103
	AB	5,670,798	09/23/97	Jan F. Schetzina	257	96
	AC	5,146,465	09/08/92	Muhammad A. Khan et al.	372	45
	AD	5,592,501	01/07/97	John A. Edmond et al.	372	45

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
DW	AE	EP0772249A	05/07/97	EP		
	AF	EP0723303A	07/24/96	EP		
	AG	EP0678945A	10/25/95	EP		

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

DW	AH	Amano, H. et al. "Improvement of Crystalline Quality of Group III Nitrides on Sapphire Using Low Temperature Interlayers", MRS Internet J. Nitride Semiconductor Res. 4A1, G10.1, 1999.
	AI	Nakamura, S. et al., "Continuous-Wave Operation of InGaN/GaN/AlGaIn-based Laser Diodes grown on GaN Substrates", Applied Physics Letters, Vol. 72, No. 16, April 20, 1998, pp. 2014-2016.
	AJ	Ohba, Y., "Fabrication and Characterization of AlGaIn/GaN Double-Heterolaser Structures on Sapphire Substrates Using Single Crystalline AlN Buffer Layers", Japan J. Physics, Vol. 37, 1998, pp.905-906.
	AK	Hofstetter, Daniel et al., "Excitation of a Higher Order Transverse Mode in an Optically Pumped In _{0.15} Ga _{0.85} N/In _{0.05} Ga _{0.95} N Multiquantum Well Laser Structure", Applied Physics Letters, Vol. 70, No. 13, March 31, 1997, pp. 1650-1652.
	AL	Nakamura, S. et al., "InGaIn/GaN/AlGaIn-based Laser Diodes with Modulation-Doped Strain-Layer Supelattices Grown on an Epitaxially Laterally Overgrown GaN Substrate", Applied Physics Letters, Vol. 72, No. 2, January 12, 1998, pp. 211-213.
	AM	Ito, K., et al., "Preparation of Al _x Ga _{1-x} N/GaN Heterostructure by MOVPE", Journal of Crystal Growth, Vol. 104, 1990, pp. 533-538.
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EXAMINER

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04/21/03

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ATTY. DOCKET NO.

10991002-4

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10/040,328

APPLICANT

Tetsuya Takeuchi et al.

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Dec. 19, 2001

GROUP

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME
	1A			
	1B			
	1C			
	1D			
	1E			
	1F			
	1G			
	1H			
	1I			
	1J			
	1K			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION	
					YES	NO
du	1L	WO 99/25030	05/20/99	PCT		
du	1M	09-199759	07/31/97	Japan	X	
	1N					
	1O					
	1P					

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du	1Q	Usui, Akira et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy", Japan Journal of Applied Physics, Vol. 36, 1997, pp. L899-902.
du	1R	Takahashi, Naoyuki, "Growth of GaN on GaAs (111)B by Mitalorganic Hydrogen Chloride VPE Using Double Buffer Layer", Japan Journal of Applied Physics, Vol. 36, 1997, pp. L1133-1135.
du	1S	Grandjean, N t al., "Si and Mg Doped GaN Layers Grown by Gas Source Molecular Beam Epitaxy Using Ammonia", Mat. Res. Soc. Symposium, Vol 482, 1998, pp. 211-216.

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04/21/03